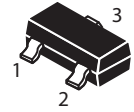
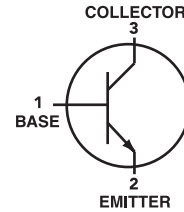


### NPN General Purpose Transistors



SOT-23

#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	$V_{CEO}$	25	Vdc
Collector-Base Voltage	$V_{CBO}$	40	Vdc
Emitter-Base Voltage	$V_{EBO}$	5.0	Vdc
Collector Current-Continuous	$I_C$	500	mAdc

#### THERMAL CHARACTERISTICS

Characteristics	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (1) $T_A=25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	225	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	556	$^\circ\text{C/W}$
Total Device Dissipation Alumina Substrate, (2) $T_A=25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	300	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	417	$^\circ\text{C/W}$
Junction and Storage, Temperature	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

#### DEVICE MARKING

S9013=J3

#### ELECTRICAL CHARACTERISTICS

Characteristics	Symbol	Min	Max	Unit
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#### OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage ( $I_C=0.1\text{mAdc}, I_B=0$ )	$V_{(BR)CEO}$	25	-	Vdc
Collector-Base Breakdown Voltage ( $I_C=100\mu\text{Adc}, I_E=0$ )	$V_{(BR)CBO}$	40	-	Vdc
Emitter-Base Breakdown Voltage ( $I_E=100\mu\text{Adc}, I_C=0$ )	$V_{(BR)EBO}$	5.0	-	Vdc
Collector Cutoff Current ( $V_{CE}=20\text{Vdc}, I_E=0$ )	$I_{CEO}$	-	0.1	$\mu\text{Adc}$
Collector Cutoff Current ( $V_{CB}=40\text{Vdc}, I_E=0$ )	$I_{CBO}$	-	0.1	$\mu\text{Adc}$
Emitter Cutoff Current ( $V_{EB}=5.0\text{Vdc}, I_C=0$ )	$I_{EBO}$	-	0.1	$\mu\text{Adc}$

1.FR-5=1.0 x 0.75 x 0.062 in

2.Alumina=0.4 x 0.3 x 0.024 in. 99.5% alumina

**S9013** **WEITRON****ELECTRICAL CHARACTERISTICS** ( $T_A=25^\circ\text{C}$  unless otherwise noted) (Continued)

Characteristics	Symbol	Min	Max	Unit
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**ON CHARACTERISTICS**

DC Current Gain ( $I_C=50\text{ mAdc}$ , $V_{CE}=1.0\text{ Vdc}$ ) ( $I_C=500\text{ mAdc}$ , $V_{CE}=1.0\text{ Vdc}$ )	$h_{FE}^{(1)}$ $h_{FE}^{(2)}$	120 40	350 -	- -
Collector-Emitter Saturation Voltage ( $I_C=500\text{ mAdc}$ , $I_B=50\text{ mAdc}$ )	$V_{CE(sat)}$	-	0.6	Vdc
Base-Emitter Saturation Voltage ( $I_C=500\text{ mAdc}$ , $I_B=50\text{ mAdc}$ )	$V_{BE(sat)}$	-	1.2	Vdc

**SMALL-SIGNAL CHARACTERISTICS**

Current-Gain-Bandwidth Product ( $I_C=20\text{ mAdc}$ , $V_{CE}=6.0\text{ Vdc}$ , $f=30\text{ MHz}$ )	$f_T$	150	-	MHz
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**CLASSIFICATION OF  $h_{FE}$** 

Rank	L	H
Range	120-200	200-350

[www.DataSheet4U.com](http://www.DataSheet4U.com)**WEITRON**<http://www.weitron.com.tw>

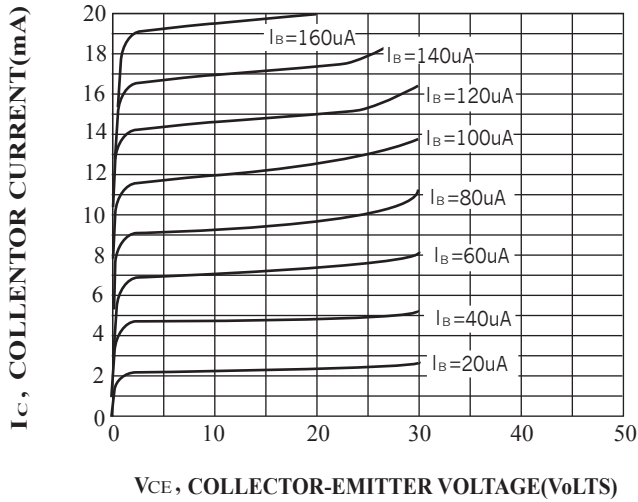


Figure1. Static Characteristic

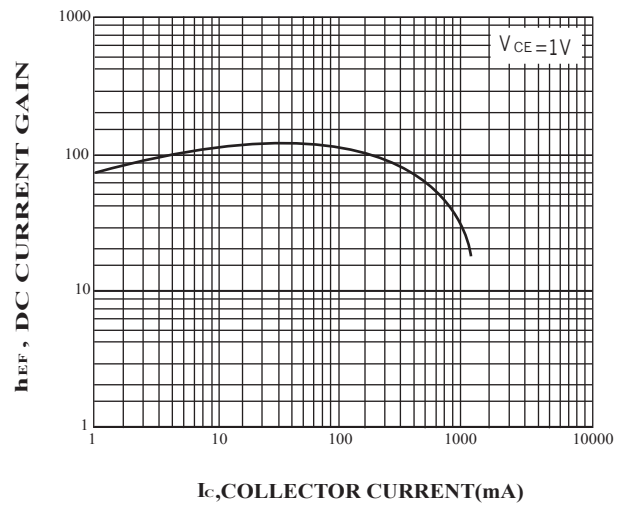


Figure2. DC current Gain

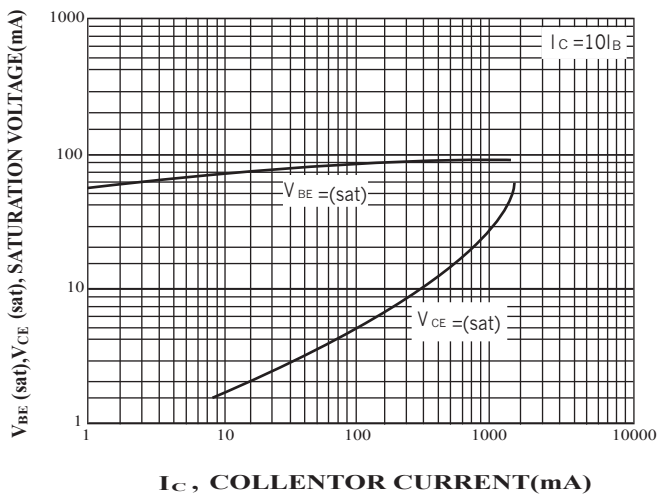


Figure3. Base-Emitter Saturation Voltage  
Collector-Emitter Saturation Voltage

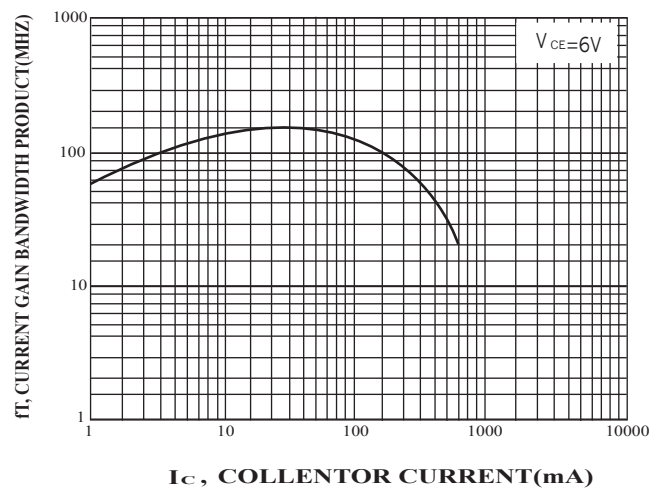


Figure4. Current Gain Bandwidth Product